

Description

The 74HC1G02 is high speed CMOS two input NOR gate using silicon gate CMOS process. With CMOS low power dissipation, it provides high-speed equivalent to LS-TTL series. The internal circuit of three stages construction with buffer provides wide noise margin and stable output.

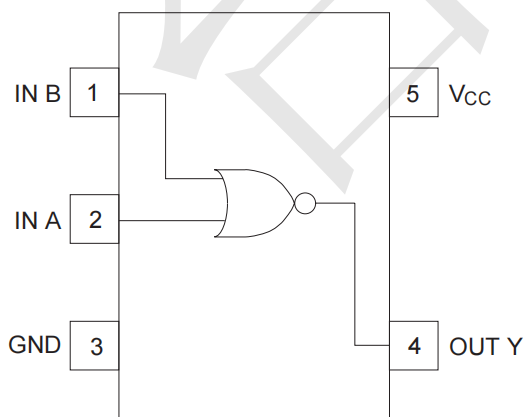
Features

- The basic gate function is lined up as Renesas uni logic series.
- Supplied on emboss taping for high-speed automatic mounting.
- Electrical characteristics equivalent to the 74HC1G02
- Supply voltage range : 2 to 6 V
- Operating temperature range : -40 to +85°C
- $|I_{OH}| = I_{OL} = 2 \text{ mA (min)}$
- Ordering Information

Ordering Information

ORDER NUMBER	PACKAGE DESCRIPTION	PACKAGE OPTION
74HC1G02GV	SOT23-5	Tape and Reel,3000
74HC1G02GW	SOT353	Tape and Reel,3000

Pin Arrangement



(Top view)

Function Table

Inputs		
A	B	Output Y
L	L	H
L	H	L
H	L	L
H	H	L

H : High level

L : Low level

Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Test Conditions
Supply voltage range	V_{CC}	–0.5 to 7.0	V	
Input voltage range ^{*1}	V_I	–0.5 to $V_{CC} + 0.5$	V	
Output voltage range ^{*1,2}	V_O	–0.5 to $V_{CC} + 0.5$	V	Output : H or L
Input clamp current	I_{IK}	±20	mA	$V_I < 0$ or $V_I > V_{CC}$
Output clamp current	I_{OK}	±20	mA	$V_O < 0$ or $V_O > V_{CC}$
Continuous output current	I_O	±25	mA	$V_O = 0$ to V_{CC}
Continuous current through V_{CC} or GND	I_{CC} or I_{GND}	±25	mA	
Maximum power dissipation P_T at $T_a = 25^\circ\text{C}$ (in still air) ^{*3}		200	mW	
Storage temperature	T_{stg}	–65 to 150	°C	

Notes: The absolute maximum ratings are values, which must not individually be exceeded, and furthermore, no two of which may be realized at the same time.

1. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 5.5 V maximum.
3. The maximum package power dissipation was calculated using a junction temperature of 150°C.

Recommended Operating Conditions

Item	Symbol	Min	Max	Unit	Test Conditions
Supply voltage range	V_{CC}	2	6	V	
Input voltage range	V_I	0	V_{CC}	V	
Output voltage range	V_O	0	V_{CC}	V	
Output current	I_{OL}	—	2.0	mA	$V_{CC} = 4.5\text{ V}$
		—	2.6		$V_{CC} = 6.0\text{ V}$
	I_{OH}	—	–2.0	mA	$V_{CC} = 4.5\text{ V}$
		—	–2.6		$V_{CC} = 6.0\text{ V}$
Input rise / fall time (10% to 90%)	t_r, t_f	0	1000	ns	$V_{CC} = 2.0\text{ V}$
		0	500		$V_{CC} = 4.5\text{ V}$
		0	400		$V_{CC} = 6.0\text{ V}$
Operating temperature	T_a	–40	85	°C	

Note: Unused or floating inputs must be held high or low.

Electrical Characteristics

Item	Symbol	V _{CC} (V)	T _a = 25°C			T _a = -40 to 85°C		Unit	Test Conditions				
			Min	Typ	Max	Min	Max						
Input voltage	V _{IH}	2.0	1.5	—	—	1.5	—	V					
		4.5	3.15	—	—	3.15	—						
		6.0	4.2	—	—	4.2	—						
	V _{IL}	2.0	—	—	0.5	—	0.5						
		4.5	—	—	1.35	—	1.35						
		6.0	—	—	1.8	—	1.8						
Output voltage	V _{OH}	2.0	1.9	2.0	—	1.9	—	V	V _{IN} = V _{IH} or V _{IL}		I _{OH} = -20 μA		
		4.5	4.4	4.5	—	4.4	—						
		6.0	5.9	6.0	—	5.9	—						
		4.5	4.18	4.31	—	4.13	—			I _{OH} = -2 mA			
		6.0	5.68	5.80	—	5.63	—			I _{OH} = -2.6 mA			
		6.0	—	0.0	0.1	—	0.1			I _{OL} = 20 μA			
	V _{OL}	4.5	—	0.0	0.1	—	0.1						
		6.0	—	0.0	0.1	—	0.1						
		4.5	—	0.17	0.26	—	0.33			I _{OL} = 2 mA			
		6.0	—	0.18	0.26	—	0.33			I _{OL} = 2.6 mA			
		Input current	I _{IN}	6.0	—	—	±0.1			—	±1.0	μA	V _{IN} = V _{CC} or GND
		Operating current	I _{CC}	6.0	—	—	1.0			—	10.0	μA	V _{IN} = V _{CC} or GND

Switching Characteristics

$T_a = 25^\circ\text{C}$

Item	Symbol	$T_a = 25^\circ\text{C}$			Unit	Test Conditions
		Min	Typ	Max		
Output rise / fall time	t_{TLH}	—	5	10	ns	Test circuit
	t_{THL}					
Propagation delay time	t_{PLH}	—	7	15	ns	Test circuit
	t_{PHL}					

($C_L = 15 \text{ pF}$, $t_r = t_f = 6 \text{ ns}$, $V_{CC} = 5 \text{ V}$)

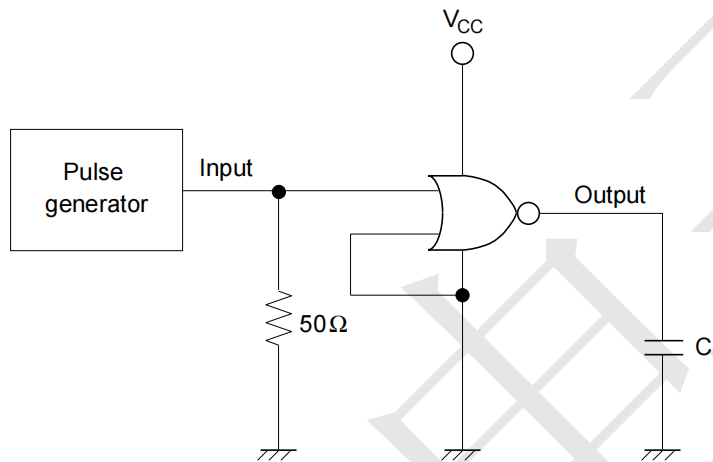
Item	Symbol	V_{CC} (V)	$T_a = 25^\circ\text{C}$			$T_a = -40 \text{ to } 85^\circ\text{C}$		Unit	Test Conditions
			Min	Typ	Max	Min	Max		
			Output rise / fall time	t_{TLH}	2.0	—	50		
	t_{THL}	4.5	—	14	25	—	31		
		6.0	—	12	21	—	26		
Propagation delay time	t_{PLH}	2.0	—	48	100	—	125	ns	Test circuit
		4.5	—	12	20	—	25		
		6.0	—	9	17	—	21		
Input capacitance	C_{IN}	—	—	2.5	5	—	5	pF	
Equivalent capacitance	C_{PD}	—	—	10	—	—	—	pF	

($C_L = 50 \text{ pF}$, $t_r = t_f = 6 \text{ ns}$)

Note: C_{PD} is equivalent capacitance inside of the IC calculated from the operating current without load (see test circuit). The average operating current without load is calculated according to the expression below.

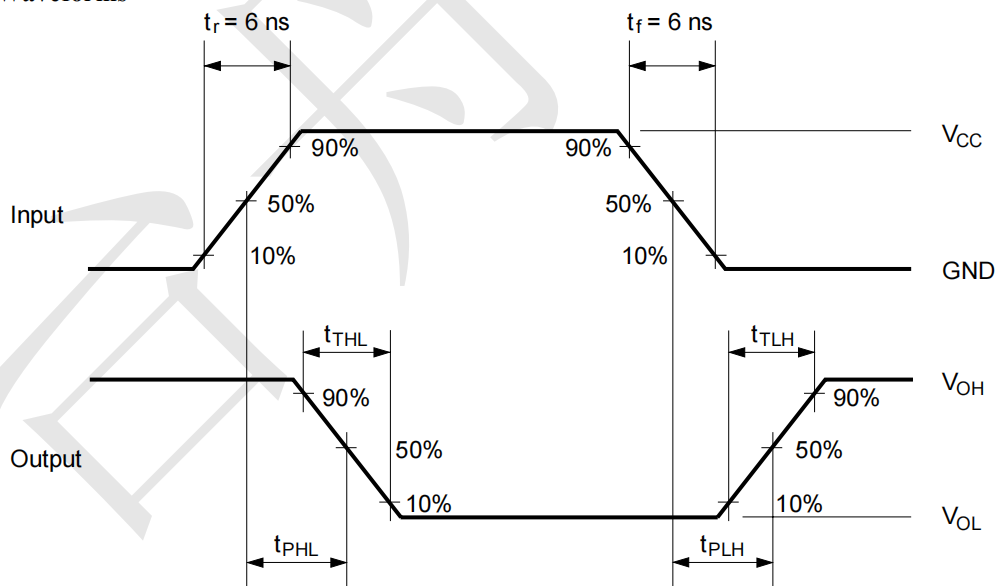
$$I_{CC}(\text{opr}) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$$

Test Circuit



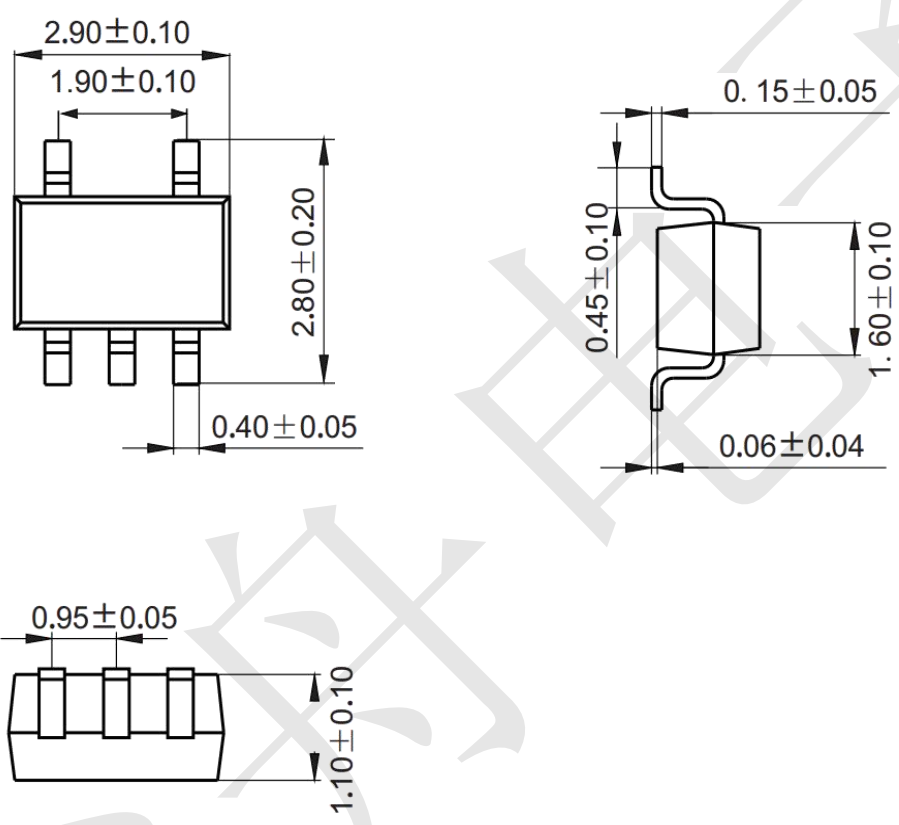
Note: 1. C_L includes probe and jig capacitance.

• Waveforms

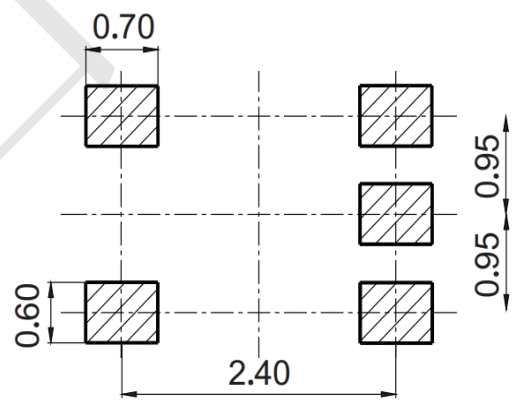


Package information

SOT23-5 (Unit: mm)

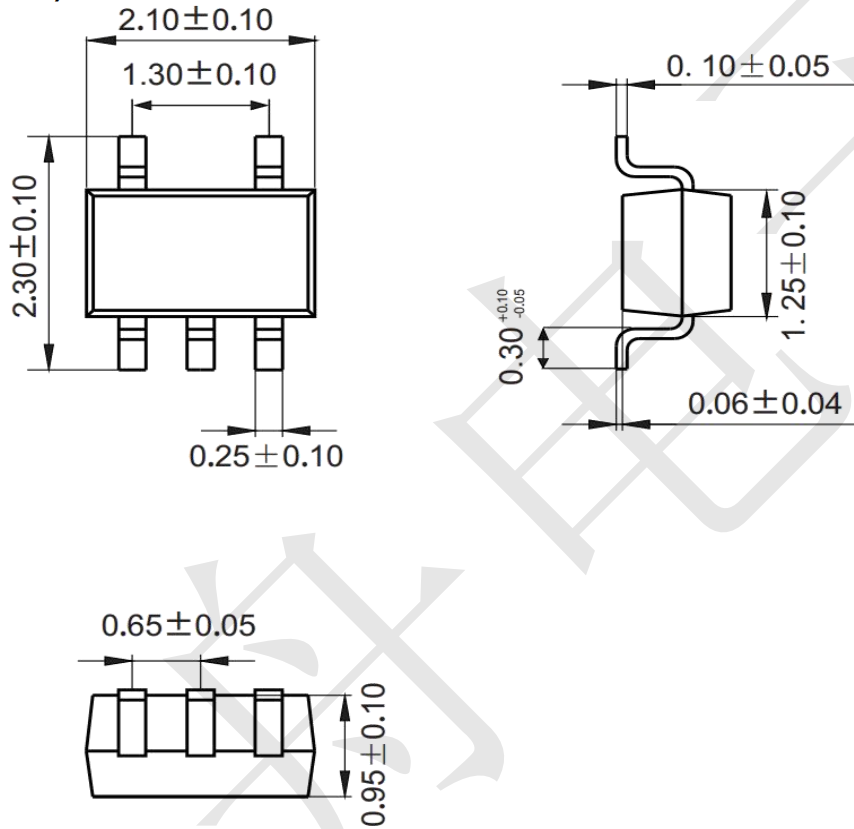


Mounting Pad Layout (Unit: mm)



Package information

SOT353 (Unit: mm)



Mounting Pad Layout (Unit: mm)

